

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









Product data sheet

Product profile

1.1 General description

The BFT25A is a silicon NPN transistor, primarily intended for use in RF low power amplifiers, such as pocket telephones and paging systems with signal frequencies up to 2 GHz.

The transistor is encapsulated in a 3-pin plastic SOT23 envelope.

1.2 Features and benefits

- Low current consumption (100 μA to 1 mA)
- Low noise figure
- Gold metallization ensures excellent reliability.

1.3 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-	8	V
V _{CEO}	collector-emitter voltage	open base		-	-	5	V
I _C	DC collector current			-	-	6.5	mA
P _{tot}	total power dissipation	up to $T_s = 165 ^{\circ}\text{C}$	<u>[1]</u>	-	-	32	mW
h _{FE}	DC current gain	$I_C = 0.5 \text{ mA}; V_{CE} = 1 \text{ V}$		50	80	200	
f _T	transition frequency	$I_{C} = 1 \text{ mA}; V_{CE} = 1 \text{ V};$ $T_{amb} = 25 \text{ °C};$ f = 500 MHz		3.5	5	-	GHz
G _{UM}	maximum unilateral power gain	I_C = 0.5 mA; V_{CE} = 1 V; T_{amb} = 25 °C; f = 1 GHz		-	15	-	dB
F	noise figure	$\begin{split} \Gamma &= \Gamma_{opt}; \ I_C = 0.5 \ mA; \\ V_{CE} &= 1 \ V; \\ T_{amb} &= 25 \ ^{\circ}C; \ f = 1 \ GHz \end{split}$		-	1.8	-	dB
		$\begin{split} &\Gamma = \Gamma_{opt}; \ I_C = 1 \ mA; \\ &V_{CE} = 1 \ V; \\ &T_{amb} = 25 \ ^{\circ}C; \ f = 1 \ GHz \end{split}$		-	2	-	dB

^[1] T_s is the temperature at the soldering point of the collector tab.



NPN 5 GHz wideband transistor

2. Pinning information

Table 2. Discrete pinning

Pin Description Simplified outline Symbol Code: V10 1 base 2 emitter					
1 base 2 emitter	Pin	Description	Simplified outline	Symbol	
base emitter	Code: V10				
	1	base		3 	
	2	emitter		1 —	
3 collector $1 \sqcup 1 \sqcup 2 \sqcup 2$	3	collector	1 2	' `	
2 sym021				2 svm021	

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
BFT25A	-	plastic surface mounted package; 3 leads	SOT23	

4. Marking

Table 4. Marking

Type number	Marking code ^[1]
BFT25A	34*

[1] * = p: Made in Hong Kong.

* = t : Made in Malaysia.

* = W : Made in China.

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	8	V
V_{CEO}	collector-emitter voltage	open base	-	5	V
V_{EBO}	emitter-base voltage	open collector	-	2	V
I _C	DC collector current		-	6.5	mA
P _{tot}	total power dissipation	up to $T_s = 165 ^{\circ}C$	[1] -	32	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	175	°C

^[1] T_s is the temperature at the soldering point of the collector tab.

NPN 5 GHz wideband transistor

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-s)}$	from junction to soldering point		<u>[1]</u> 260	K/W

^[1] T_s is the temperature at the soldering point of the collector tab.

7. Characteristics

Table 7. Characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{CBO}	collector cut-off current	$I_E = 0 A; V_{CB} = 5 V$	-	-	50	nA
h _{FE}	DC current gain	$I_C = 0.5 \text{ mA}; V_{CE} = 1 \text{ V}$	50	80	200	
f _T	transition frequency	$I_{C} = 1 \text{ mA}; V_{CE} = 1 \text{ V};$ $T_{amb} = 25 \text{ °C};$ f = 500 MHz	3.5	5	-	GHz
C _{re}	feedback capacitance	$I_C = I_c = 0 A; V_{CB} = 1 V;$ f = 1 MHz	-	0.3	0.45	pF
G _{UM}	maximum unilateral power gain	$I_{C} = 0.5 \text{ mA}; V_{CE} = 1 \text{ V};$ $T_{amb} = 25 \text{ °C}; f = 1 \text{ GHz}$	[1] -	15	-	dB
F	noise figure	$\begin{split} \Gamma &= \Gamma_{\text{opt}}; \ I_{\text{C}} = 0.5 \ \text{mA}; \\ V_{\text{CE}} &= 1 \ \text{V}; \\ T_{\text{amb}} &= 25 \ ^{\circ}\text{C}; \ f = 1 \ \text{GHz} \end{split}$	-	1.8	-	dB
		$\Gamma = \Gamma_{opt}$; $I_C = 1$ mA; $V_{CE} = 1$ V; $T_{amb} = 25$ °C; $f = 1$ GHz	-	2	-	dB

^[1] $\;\;G_{UM}$ is the maximum unilateral power gain, assuming S_{12} is zero and

$$G_{\text{UM}} = 10 \log \frac{\left|S_{21}\right|^2}{(I - \left|S_{11}\right|^2)(I - \left|S_{22}\right|^2)} dB$$

NPN 5 GHz wideband transistor

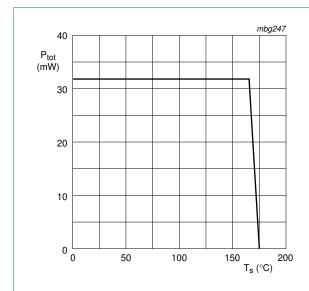
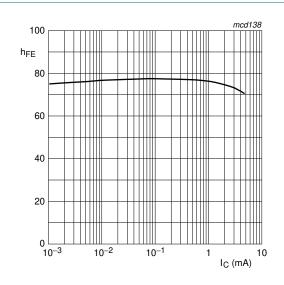
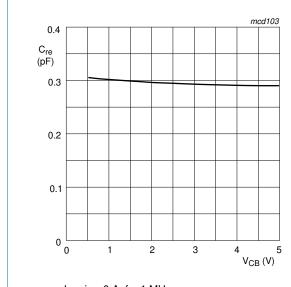


Fig 1. Power derating curve.



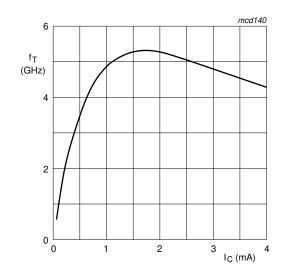
 $V_{CE} = 1 V.$

Fig 2. DC current gain as a function of collector current.



 $I_C = i_c = 0 \text{ A}; f = 1 \text{ MHz}.$

Fig 3. Feedback capacitance as a function of collector-base voltage.

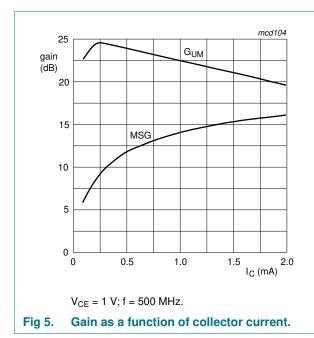


 V_{CE} = 1 V; T_{amb} = 25 °C; f = 500 MHz.

Fig 4. Transition frequency as a function of collector current.

<u>Figure 5, 6, 7</u> and 8, G_{UM} = maximum unilateral power gain; MSG = maximum stable gain.

NPN 5 GHz wideband transistor



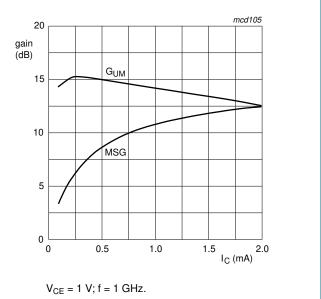
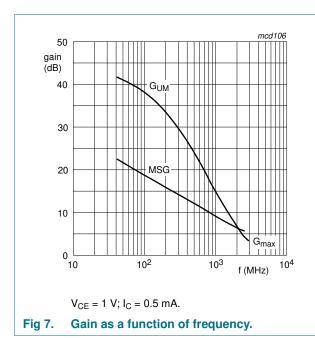


Fig 6. Gain as a function of collector current.



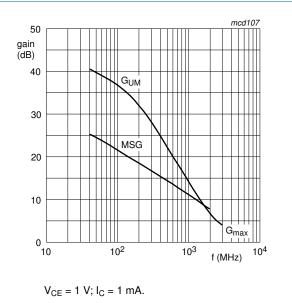


Fig 8. Gain as a function of frequency.

NPN 5 GHz wideband transistor

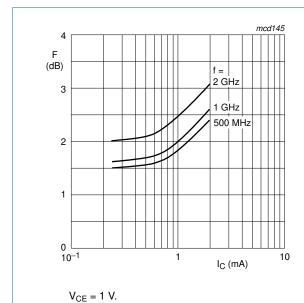


Fig 9. Minimum noise figure as a function of collector current.

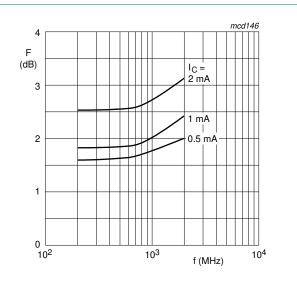
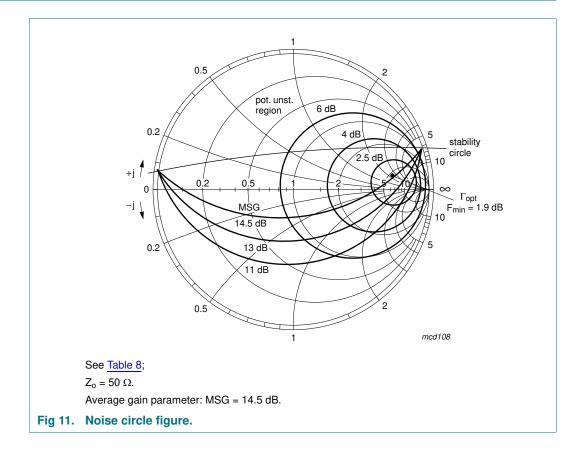


Fig 10. Minimum noise figure as a function of frequency.

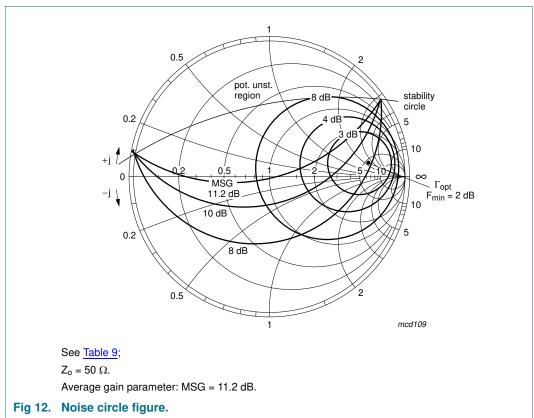
 $V_{CE} = 1 V$.



NPN 5 GHz wideband transistor

Table 8. Noise parameters

f (MHz)	V _{CE} (V)	I _C (mA)	F _{min} (dB)	Γ_{opt}		R _n /50
				(mag)	(ang)	
500	1	1	1.9	0.79	4	2.5



Noise parameters

Table 9.

f (MHz)	V _{CE} (V)	I _C (mA)	F _{min} (dB)	Γ_{opt}		R _n /50
				(mag)	(ang)	
1000	1	1	2	0.74	8	2.6

NPN 5 GHz wideband transistor

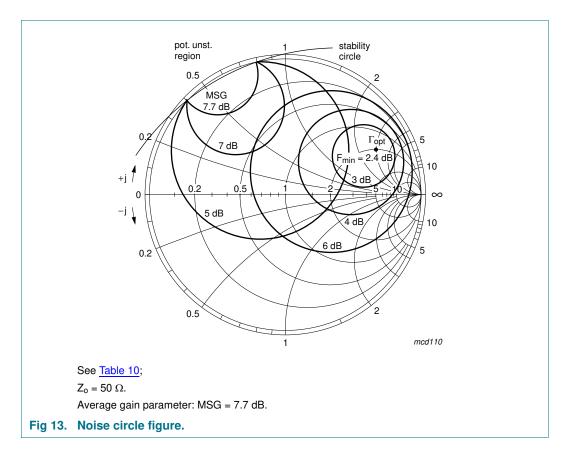
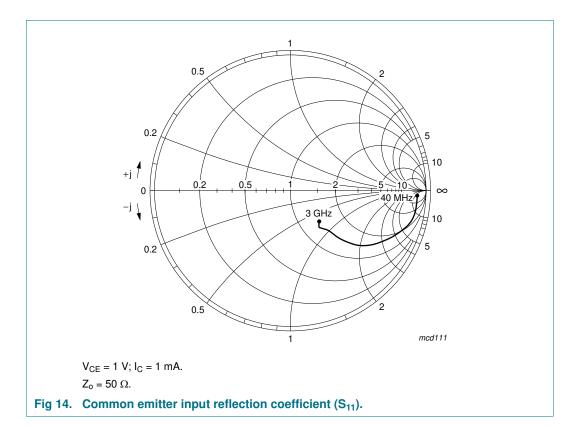
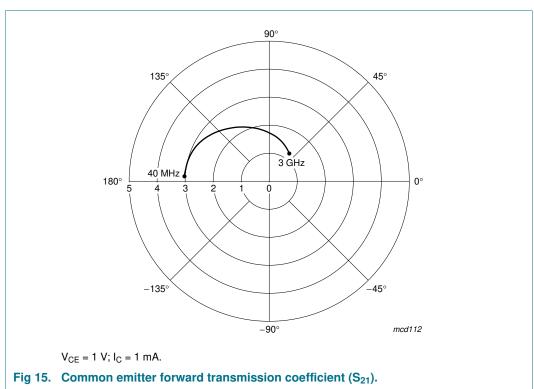


Table 10. Noise parameters

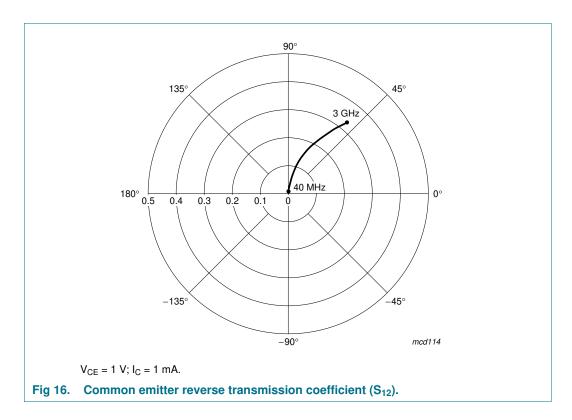
f (MHz)	V _{CE} (V)	I _C (mA)	F _{min} (dB)	Γ_{opt}		R _n /50
				(mag)	(ang)	
2000	1	1	2.4	0.72	26	1.7

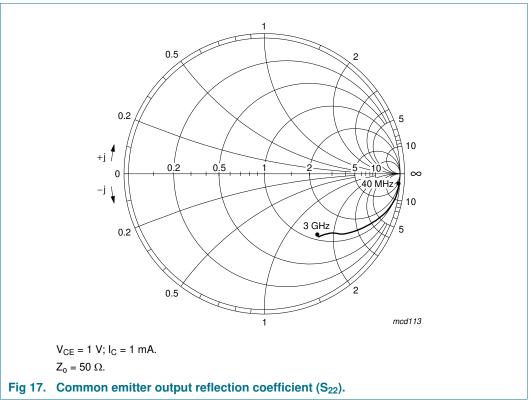
NPN 5 GHz wideband transistor





NPN 5 GHz wideband transistor





8. Package outline

Plastic surface-mounted package; 3 leads

SOT23

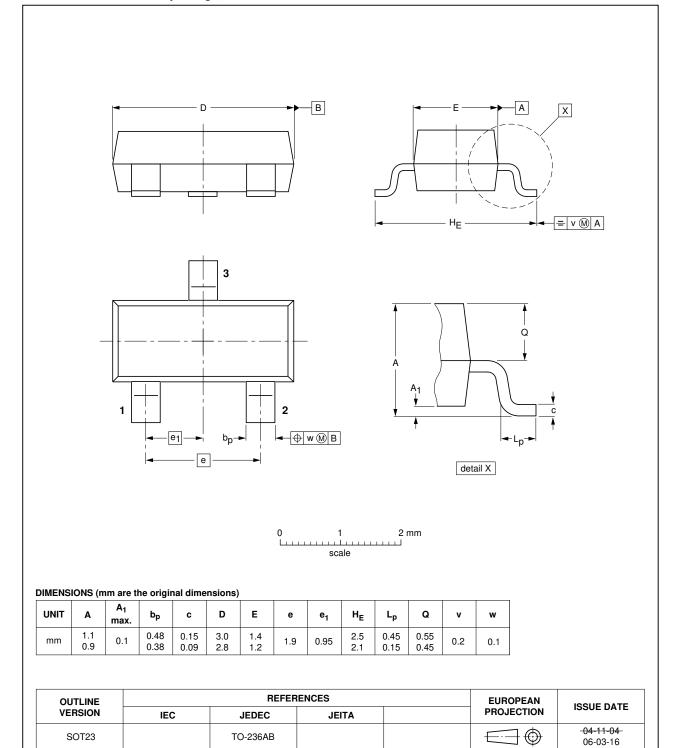


Fig 18. Package outline.

BFT25A **NXP Semiconductors**

NPN 5 GHz wideband transistor

Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BFT25A v.5	20110912	Product data sheet	-	BFT25A v.4	
Modifications:	guidelines of	f this data sheet has been red NXP Semiconductors.		·	
	 Legal texts have been adapted to the new company name where appropriate. 				
	 Package out 	line drawings have been upda	ted to the latest vers	ion.	
BFT25A v.4 (9397 750 13399)	20040706	Product data sheet	-	BFT25A_CNV v.3	
BFT25A_CNV v.3	19971205	Product specification	-	-	

12 of 15

NPN 5 GHz wideband transistor

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

10.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

10.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or

malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

RFT25A

All information provided in this document is subject to legal disclaimers.

© NXP B.V. 2011. All rights reserved.

NPN 5 GHz wideband transistor

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Non-automotive qualified products — Unless this data sheet expressly states that this specific NXP Semiconductors product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. NXP Semiconductors accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without NXP Semiconductors' warranty of the

product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond NXP Semiconductors' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies NXP Semiconductors for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond NXP Semiconductors' standard warranty and NXP Semiconductors' product specifications.

10.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

11. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

BFT25A **NXP Semiconductors**

NPN 5 GHz wideband transistor

12. Contents

1	Product profile	. 1
1.1	General description	. 1
1.2	Features and benefits	. 1
1.3	Quick reference data	. 1
2	Pinning information	2
3	Ordering information	. 2
4	Marking	2
5	Limiting values	2
6	Thermal characteristics	. 3
7	Characteristics	. 3
8	Package outline	11
9	Revision history	12
10	Legal information	13
10.1	Data sheet status	13
10.2	Definitions	13
10.3	Disclaimers	13
10.4	Trademarks	14
11	Contact information	14
12	Contents	15

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.